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June 25, 2009

#### **15-W MONO CLASS-D AUDIO POWER AMPLIFIER**

#### **GENERAL DESCRIPTION**

The TMPA401DM is a bridged-tied (BTL) Class-D audio amplifier for driving speakers with high power efficiency. It can drive  $4\Omega$ ,  $6\Omega$ ,  $8\Omega$  or  $16\Omega$  speakers. The output power can be up to 15W. No external heat-sink is necessary.

The gain of the amplifier is defined by input resistance. The internally fully differential input structure provides good common mode rejection and power supply rejection.

Thermal protection and short-circuit protection are integrated for safety purpose.

The internal de-pop circuitry eliminates pop noise at power-up & shutdown operations.

#### **APPLICATIONS**

LCD Monitors, TVs, DVD Players and Powered Speakers

#### PACKAGE

TSSOP20 available, pb free [RoHS]

#### PART NO.

TMPA4010DMHBT [Tube]

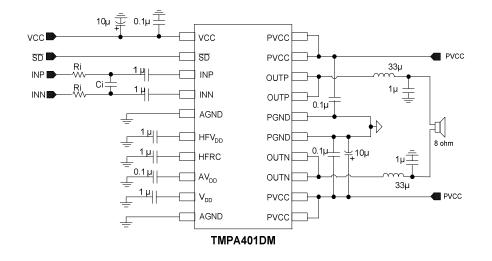
TMPA4010DMHBR [Tape & Reel]

#### **REFERENCE CIRCUIT**

#### FEATURES

- Output Power Maximum 15W at RL=6Ω,VCC=15V,BTL Rating 10W at RL=4Ω,VCC=12V,BTL
- Power efficiency is up to 82%
- ◆ Low Working Voltage Down To 5V
- Time delay for de-pop control
- Thermal Protection
- Output Pin Short-Circuit Protection
- Differential / Single-Ended Input
- Low Supply Current (5mA Typical at 12V)
- ♦ Low Current in Shutdown Mode (<1µA Typical)</p>
- ◆ Separate VCC & PVCC

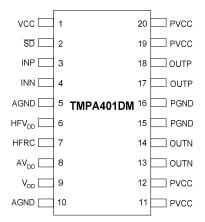
For best performance, please refer to http://www.taimec.com.tw/English/EVM.htm http://www.class-d.com.tw/English/EVM.htm for PCB layout.



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#### **TOP VIEW**



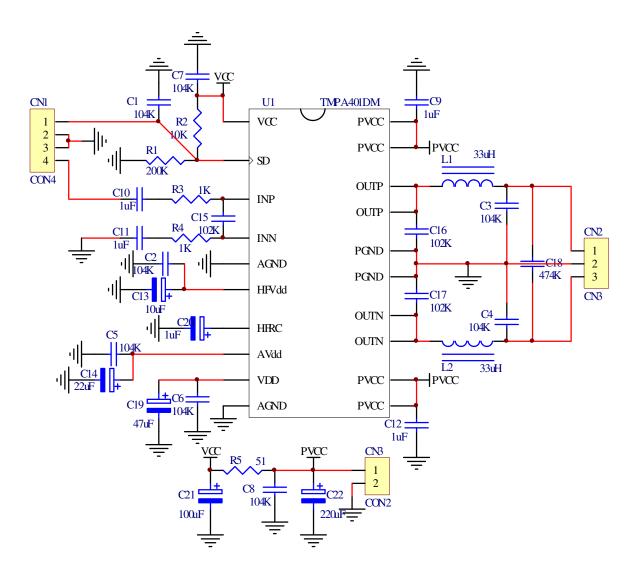
## (Please email david@taimec.com.tw for complete datasheet.)

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Note that the external components or PCB layout should be designed not to generate abnormal voltages to the chip to prevent from latch up which may cause damage to the device.



# **Typical Application**





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#### **TERMINAL FUNCTIONS**

TERMINAL		1/0			
NAME	PIN NO	I/O	DESCRIPTION		
AGND	5,10	_	Analog ground		
AVdd	8	I	5-V analog power supply		
HFRC	7	I	De-pop control		
HFVDD	6	0	2.5-V Reference for convenience of single-ended input		
INN	4	Ι	Negative differential input		
INP	3	I	Positive differential input		
OUTN	13,14	0	Negative output		
OUTP	17,18	0	Positive output		
PGND	15,16	_	Power ground		
PVCC	11,12,19,20	_	Power supply for output MOS (5V to 15V)		
Vcc	1	_	High-voltage power supply (5V to 15V)		
Vdd	9	0	5-V Reference output(25-mA)		
SD	2	I	Shutdown (Low valid)		

#### **ABSOLUTE MAXIMUM RATINGS**

Over operating free-air temperature range unless otherwise noted(1)

Supply veltage Dias Vac (Land O)	In normal mode	-0.3V to 17V	V
Supply voltage, PVcc, Vcc (Iload=0)	In shutdown mode	-0.3V to 17V	V
Input voltage, SD	-0.3V to Vcc+0.3V	V	
Input voltage, INN, INP	-0.3V to 5V	V	
Continuous total power dissipation	See package dissipation ra	itings	
Operating free-air temperature, TA	-20 to 85	°C	
Operating junction temperature, TJ	-20 to 150	°C	
Storage temperature, Tstg	-40 to 150	°C	

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions "is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

# **RECOMMENDED OPERATING CONDITIONS**

		MIN	MAX	UNIT
Supply voltage, Vcc	PVcc, Vcc	5	15	V
High-level input voltage, Vн	SD	2.0		V
Low-level input voltage, Vı∟	SD		0.8	V
Operating free-air temperature, TA	-20	85	°C	

#### PACKAGE DISSIPATION RATINGS

PACKAGE	DERATING	Ta ≤ 25 °C	TA = 70 ℃	TA = 85 ℃
	FACTOR	POWER RATING	POWER RATING	POWER RATING
TSSOP20(FD)	30 mW/ °C	3.75W	2.4W	1.95W

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#### **DC CHARACTERISTICS**

 $T_A=25 \text{ °C}, V_{CC}=15V, R_L=8\Omega$  speaker (unless otherwise noted)

	TEST CONDITIONS		MIN	TYP	MAX	UNIT		
Vos	BTL Output offset voltage	INN and INP AC grounded Gain=20dB			25	100	mV	
HFVdd	Half VDD reference output	No load			0.5x AVdd		V	
AVdd/Vdd	5-V Regulated voltage	Io=0 to 25mA, SD =High, Vcc=5V to 15V		4.5	5.0	5.5	V	
		SD=High, Vcc= 12VSD=High, Vcc= 15V			5	10		
					8	16		
ICC(SD)	Supply current in shutdown mode	de SD =0V, Vcc= 9v~15v			0.2	1	uA	
		Vcc=15V	High side		600			
r <sub>ds(on)</sub>	Drain-source on-state resistance	Io=1A, Low side		500		mΩ		
			Total		1100			
		Ri=40k			22			
*Gain		Ri=20k Ri=10k Ri= 0k			25.5		dB	
Guin	Voltage Gain				28			
					31.5			
Ін	High-level input current	VI =2V( SD ), Vcc=5~15V				20	uA	
lı.	Low-level input current	VI =0V( SD ), Vcc=5~15V				1	uA	
fosc	Oscillator frequency	Vcc=5~15V		200		300	kHz	
Zi	Input resistance of INN/INP				20		kΩ	

\*Gain= $\frac{750k}{Ri+20K}$  (Vcc=15V), Gain= $\frac{600k}{Ri+20K}$  (Vcc=12V), Ri : external input resistance of INP/INN inputs

## **AC CHARACTERISTICS**

 $T_A=25 \text{ °C}, V_{CC}=15V, R_L=8\Omega$  speaker (unless otherwise noted)

PARAMETER		TES	TEST CONDITIONS		TYP	MAX	UNIT	
			15V	Not allowed		d		
		R∟=4Ω	12V		10.5		W	
			9V		6.2			
			15V	N	laximum 1	5	7	
	Continuous output power	R∟=6Ω	12V		9.6		W	
PO(max)	(r.m.s) at 1kHz,		9V		5.4			
I O(max)	(Limited by thermal condition)		15V		13			
	(, ,	R∟=8Ω	12V		8.2		W	
			9V		4.5			
		RL=16Ω	15V		7.8			
			12V		5		W	
			9V		2.71			
	Total harmonic distortion plus noise	Vcc=9V, PO=3W, RL=6Ω, f=1kH		0.33				
		Vcc=12V, F	Vcc=12V, PO=7W, RL=6Ω, f=1kHz		0.4			
		Vcc=15V, F	PO=12W, RL=6Ω, f=1kHz		0.47		<u> </u>	
THD+N		Vcc=9V, P	Vcc=9V, PO=2W, RL=8Ω, f=1kHz		0.26		%	
		Vcc=12V, F	Vcc=12V, PO=6W, RL=8Ω, f=1kHz		0.3			
		Vcc=15V, F	Vcc=15V, PO=9.5W, RL=8Ω, f=1kHz		0.42			
Vn	Output noise	Vcc=12V, F Gain=20dE		-70		dB		

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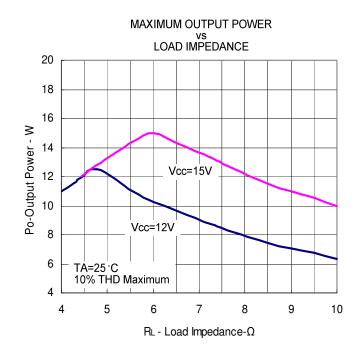


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SNR	Signal-to-noise ratio	Maximum output at THD+N<0.5%, f=1kHz	85	dB
Crosstalk	Crosstalk between outputs	Vcc=12V, Po=1W RL=8Ω	-60	dB
	Thermal trip point		145	°C
	Thermal hysteresis		25	∘C





#### DETAILED DESCRIPTION

#### Efficiency

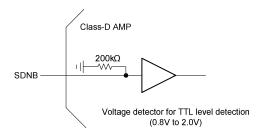
The output transistors of a class D amplifier act as switches. The power loss is mainly due to the turn on resistance of the output transistors when driving current to the load. As the turn on resistance is so small that the power loss is small and the power efficiency is high. With 8 ohm load the power efficiency can be better than 82%.

#### PCB layout for power dissipation

No heat sink is necessary for power dissipation. However the PCB layout should be well designed to dissipate heat for high output power. With 80% power efficiency the generated heat when driving 15 watts to the 8 ohm load is about 3.75 watts. The heat can be carried out through the thermal pad of the device to the PCB. To ensure proper dissipation of heat the PCB has to have heat path from the bottom of the device which is soldered to the PCB. The area of the metal on the PCB for heat dissipation should be big enough. It is suggested that both sides of the PCB are used for power dissipation.

#### Shutdown

The shutdown mode reduces power consumption. A LOW at shutdown pin forces the device in shutdown mode and a HIGH forces the device in normal operating mode. Shutdown mode is useful for power saving when not in use. This function is useful when other devices like earphone amplifier on the same PCB are used but class D amplifier is not necessary. Internal circuit for shutdown is shown below.



## HFRC (pop-less)

HFRC provides a way of soft start up delay. A half\_Vcc voltage detector is integrated to detect a RC charge up. The resistor of 320k ohms of the RC circuit is also integrated in the chip but the capacitor is externally hooked up. For C=1uF the half\_Vcc delay is

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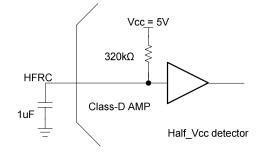
1-e<sup>-t/RC</sup>=0.5

or

e<sup>-t/RC</sup>=0.5

that is

 $t = -RC ln (0.5) = (320k \times 1u) (0.693) = 0.22 seconds$ 



#### Differential input VS single ended input

Differential input offers better noise immunity over single ended input. A differential input amplifier suppresses common noise and amplifies the difference voltage at the inputs. For single ended applications just tie the negative input end of the balanced input structure to ground. If external input resistors are used, the negative input has to be grounded with a series resistor of the same value as the positive input to reduce common noise.

#### Voltage gain

The voltage gain can be set through input resistance connecting to input pins. Lower input resistance can be used for higher gain. The voltage gain is defined by (800k ohms)/(Ri+20k ohms) at Vcc=15V without loading, where 20k ohms is internal resistance and Ri is external series resistance of the input pin. If Ri is not used (Ri=0 ohm) the voltage gain is (800k ohms)/(20k ohms) or 32dB. Insert Ri if lower gain is preferable. For example if Ri=30k ohms then voltage is (800k ohms)/(30k+20k ohms) or 24dB. For best result the input resistors should be well matched. Matched resistors are also required even for single ended input configuration for low noise.

#### Input filter

AC coupling capacitors are required to block the DC voltage from the device. They also define the –3db frequency at the low frequency side.

The –3db frequency of the low frequency side is

 $f-3db = 1/(2 \pi R C)$ 

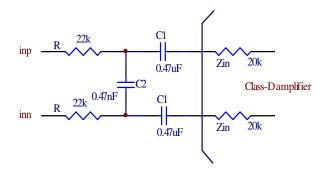
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where C is the AC coupling capacitance and R is the total resistance in series with C.

Note that R=Zin(internal resistance) + Rext(external resistance)

Also note that the internal input resistance of INN/INP is 20K ohms.

In the following diagram Rext=22k ohms, Zin=20k ohms and C=C1=0.47uF. Thus the -3db frequency at the low frequency side is about 8Hz.



A bypass capacitor placed in between the positive signal path and negative signal path is to attenuate the high frequencies. It defines the –3bd frequency at the high frequency side. The input filter becomes a band pass filter.

The -3db frequency of the high frequency side is

f–3db=1/(2  $\pi$  RC)

where C is the bypass capacitance and R is the total resistance in parallel with C.

In this example Rext=22k ohms, Zin=20k ohms and C=C2=0.47nF. Thus the -3db frequency at the high frequency side is about 16kHz.

# Input filter

Since the input pins of the device have high impedance it is suggested that an input filter is incorporated as shown in the diagram. The AC coupling capacitors are used to block the DC voltage from the device. They also define the –3db frequency at the low frequency side. A bypass capacitor placed in between the positive signal path and negative signal path is to attenuate the high frequencies. It defines the –3db frequency at the high frequency side. The input filter becomes a band pass filter.

The -3db frequency of the low frequency side is

 $f-3db = 1/2 \pi R C$ 

where C is the AC coupling capacitance(1uF) and R is the total resistance in series with C.



The -3db frequency of the high frequency side is

 $f-3db = 1/2 \pi R C$ 

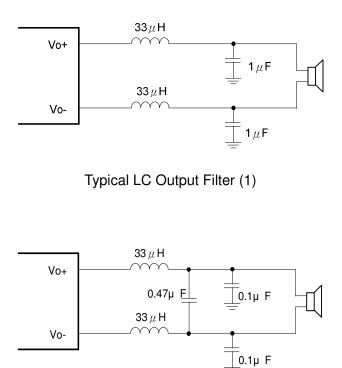
where C is the bypass capacitance(1nF) and R is the total resistance in parallel with C. Note that there is 20K input resistor integrated in the chip for each input INP/INN.

# **Output filter**

Ferrite bead filter can be used for EMI purpose. The ferrite filter reduces EMI around 1 MHz and higher(FCC and CE only test radiated emissions greater than 30 MHz). When selecting a ferrite bead, choose one with high impedance at high frequencies, but low impedance at low frequencies.

Use an LC output filter if there are low frequency ( <1 MHz) EMI sensitive circuits and/or there are long wires from the amplifier to the speaker. EMI is also affected by PCB layout and the placement of the surrounding components.

The suggested LC values for different speaker impendence are showed in following figures for reference.



Typical LC Output Filter (2)



## Over temperature protection

A temperature sensor is built in the device to detect the temperature inside the device. When a high temperature around 145  $^{\circ}$ C and above is detected the switching output signals are disabled to protect the device from over temperature. Automatic recovery circuit enables the device to come back to normal operation when the internal temperature of the device is below around 120  $^{\circ}$ C.

#### Over current protection

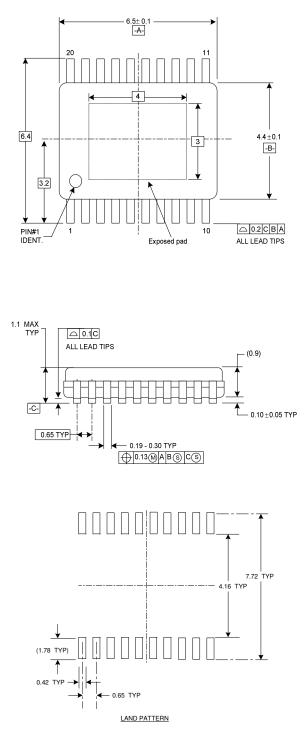
A current detection circuit is built in the device to detect the switching current of the output stages of the device. It disables the device when the current is beyond about 3.5amps. It protects the device when there is an accident short between outputs or between output and ground pins It also protects the device when an abnormal low impedance is tied to the output. High current beyond the specification may potentially causes electron migration and permanently damage the device. Shutdown or power down is necessary to resolve the protection situation. There is no automatic recovery from over current protection.



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# Physical Dimensions (IN MILLIMETERS)



TSSOP20



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